



# 《风光欣》技术资料

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## 2SD882

## NPN EPITAXIAL SILICON TRANSISTOR

### \*Features

High  $h_{FE}=160\sim320$

Low Collector Saturation Voltage

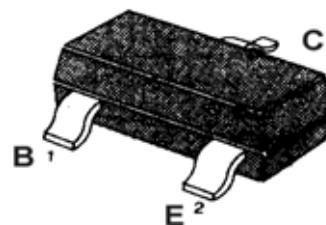
$V_{CE(sat)}=0.5V(\text{Max.})$  ( $I_C=500mA, I_B=20mA$ )

Complementary Pair With 2SB772

### ABSOLUTE MAXIMUM RATINGS( $T_A=25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter -Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	2	A
Collector Dissipation	$P_C$	225	mW
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	

SOT-23



### ELECTRICAL CHARACTERISTICS ( $T_A=25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_C=500\mu A, I_E=0$	30			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=1mA, I_B=0$	25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=50\mu A, I_C=0$	5			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB}=20V, I_E=0$			500	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			500	nA
DC Current Gain	$h_{FE}$	$V_{CE}=1V, I_C=50mA$	160		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$			0.5	V
Transition Frequency	$f_T$	$V_{CE}=5V, I_C=10mA$		120		MHz
Collector Output Capacitance	$C_{ob}$	$f=1MHz, V_{CB}=10V, I_E=0$		13		pF

DEVICE MARKING : 2SD882 = D8